

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	510 410	mA
	t < 10s	T _A = +25°C T _A = +70°C	I _D	610 490	mA
Continuous Drain Current (Note 5) V _{GS} = 1.8V	Steady State	T _A = +25°C T _A = 70°C	I _D	380 300	mA
	t < 10s	T _A = +25°C T _A = +70°C	I _D	450 360	mA
Pulsed Drain Current (Note 6)			I _{DM}	800	mA

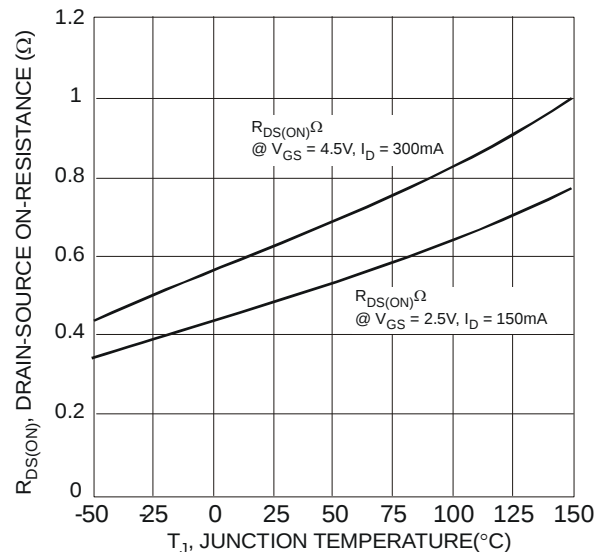
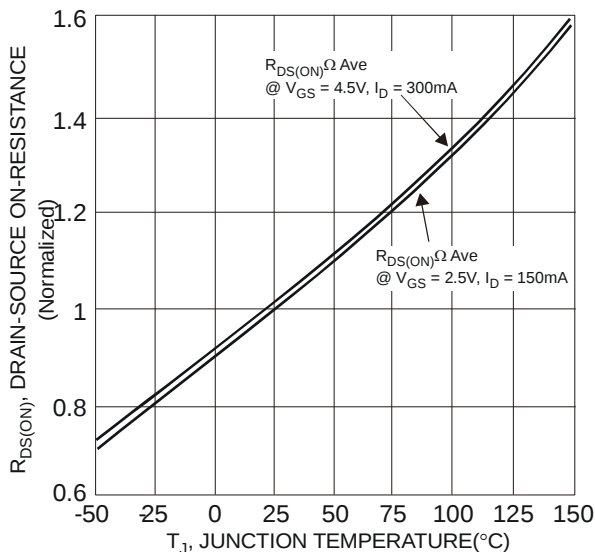
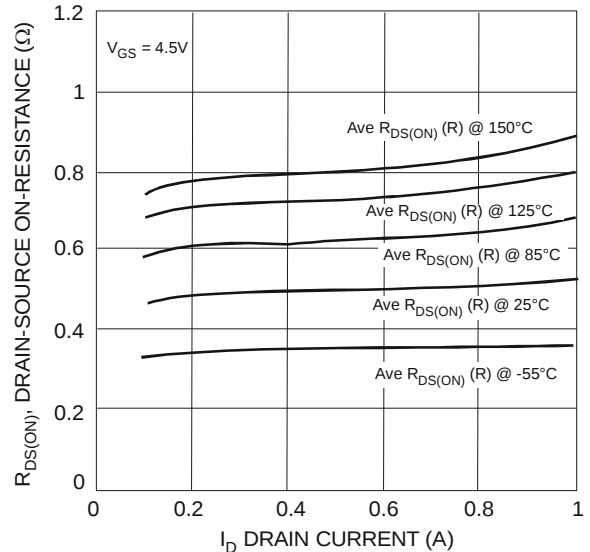
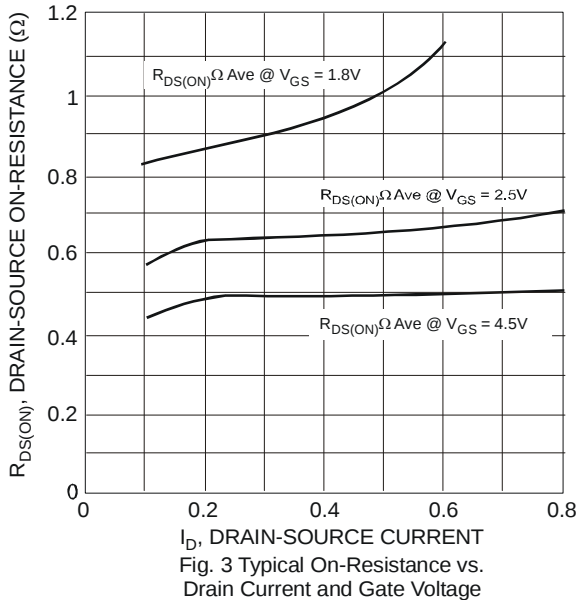
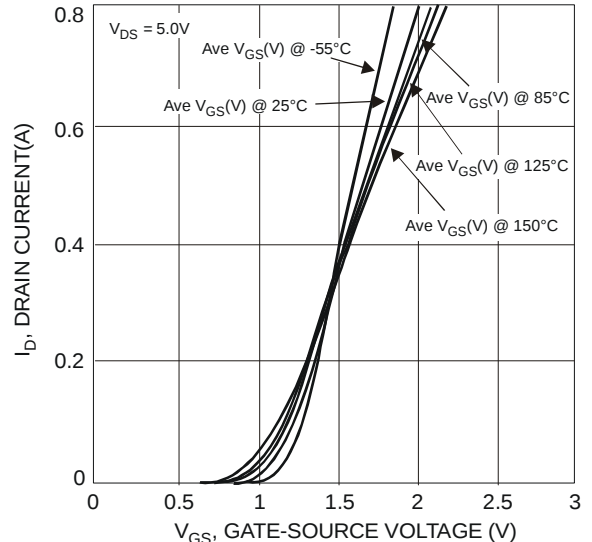
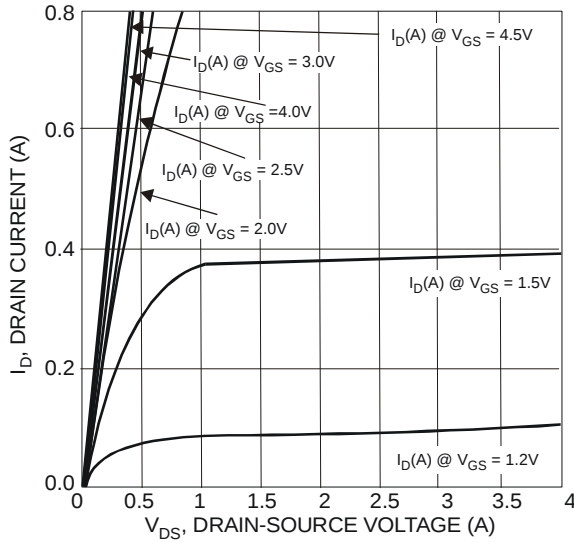
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	Steady state	P _D	400	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R _{θJA}	310	°C/W
	t < 10s		220	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current @T _C = +25°C	I _{DSS}	—	—	100	nA	V _{DS} = 16V, V _{GS} = 0V
		—	—	50		V _{DS} = 5V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±5V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	0.4	—	1.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	0.60	0.99	Ω	V _{GS} = 4.5V, I _D = 100mA
		—	0.75	1.2		V _{GS} = 2.5V, I _D = 50mA
		—	0.90	1.8		V _{GS} = 1.8V, I _D = 20mA
		—	1.2	2.4		V _{GS} = 1.5V, I _D = 10mA
		—	2.0	—		V _{GS} = 1.2V, I _D = 1mA
Forward Transfer Admittance	Y _{fs}	180	—	—	mS	V _{DS} = 10V, I _D = 400mA
Diode Forward Voltage	V _{SD}	-	0.6	1.0	V	V _{GS} = 0V, I _S = 150mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	27.6	55.2	pF	V _{DS} = 16V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	4.0	8.0	pF	
Reverse Transfer Capacitance	C _{rss}	—	2.8	5.6	pF	
Total Gate Charge	Q _g	—	0.5	—	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 250mA
Gate-Source Charge	Q _{gs}	—	0.07	—	nC	
Gate-Drain Charge	Q _{gd}	—	0.07	—	nC	
Turn-On Delay Time	t _{D(on)}	—	4.0	—	ns	V _{DD} = 10V, V _{GS} = 4.5V, R _L = 47Ω, R _G = 10Ω, I _D = 200mA
Turn-On Rise Time	t _r	—	3.3	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	19.0	—	ns	
Turn-Off Fall Time	t _f	—	6.4	—	ns	

- Notes:
5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 6. Device mounted on minimum recommended pad layout test board, 10μs pulse duty cycle = 1%.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.



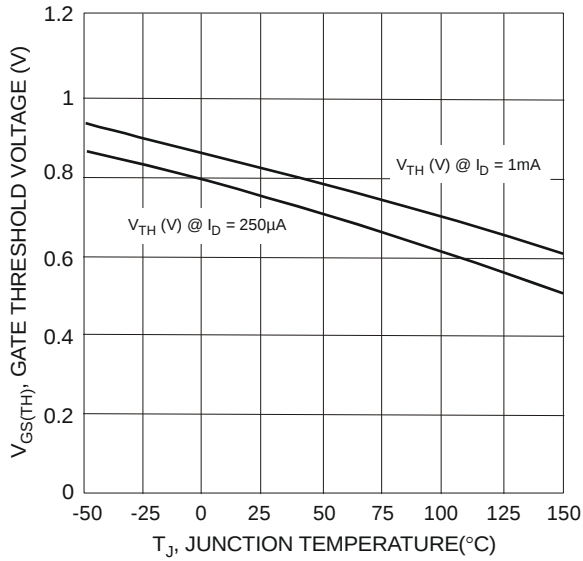


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

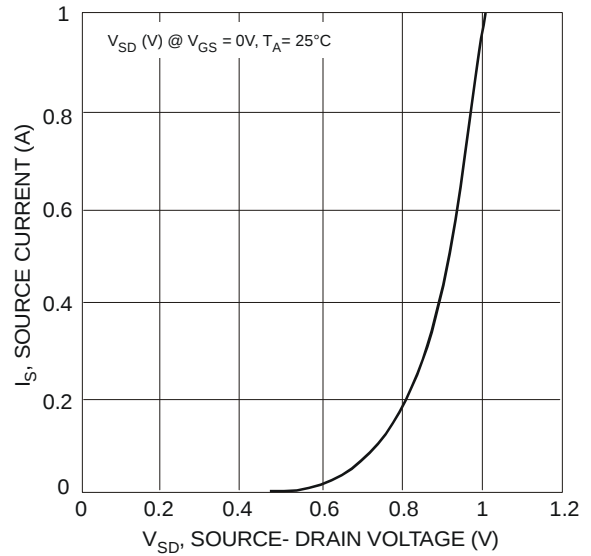


Fig. 8 Diodes Forward Voltage vs. Current

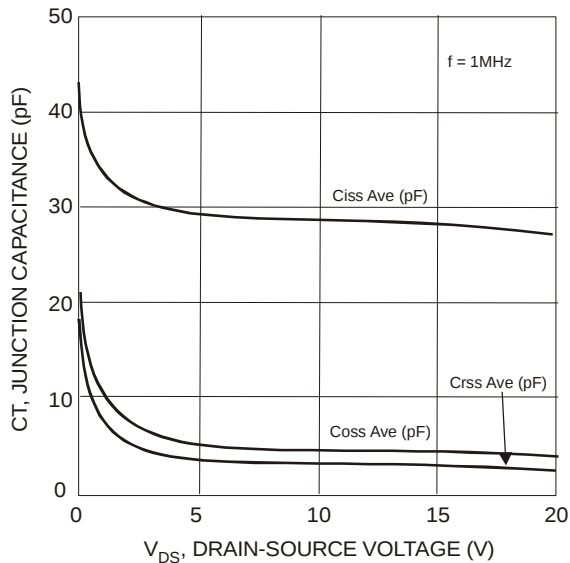


Fig. 9 Typical Junction Capacitance

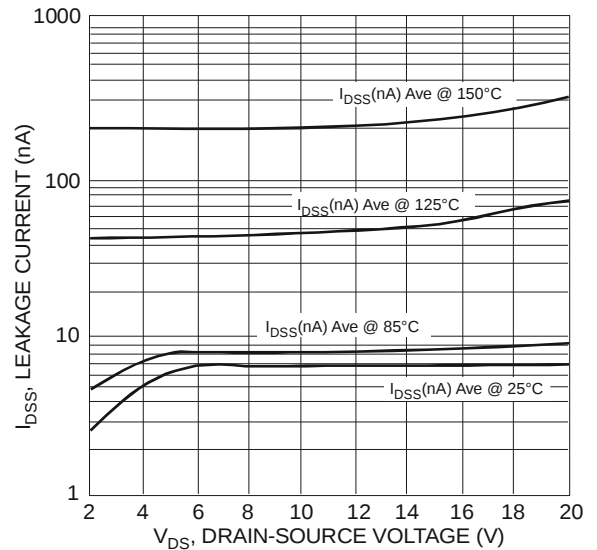


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

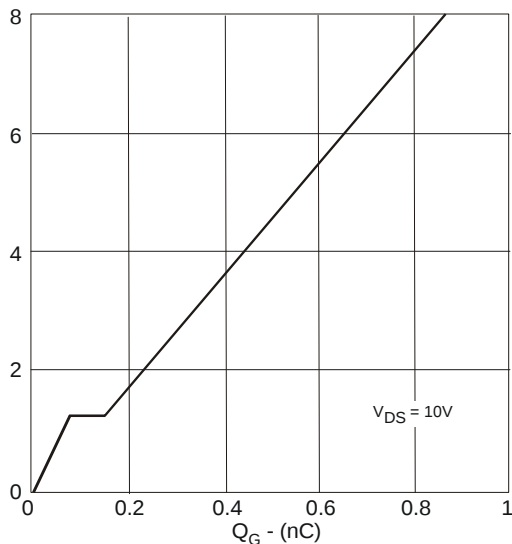
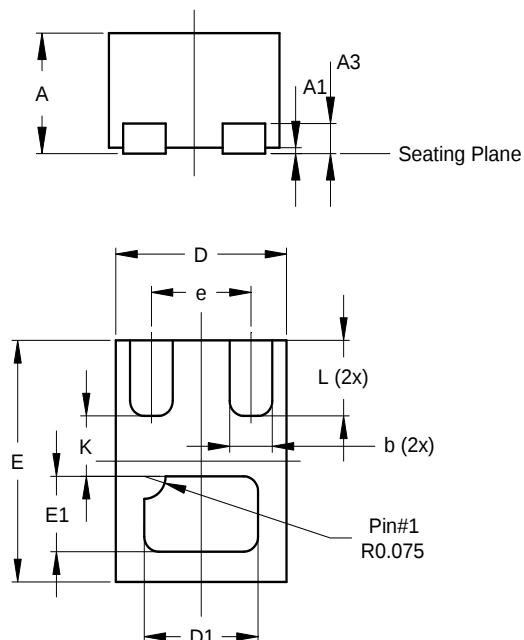


Fig. 11 Gate Charge Characteristics

Package Outline Dimensions

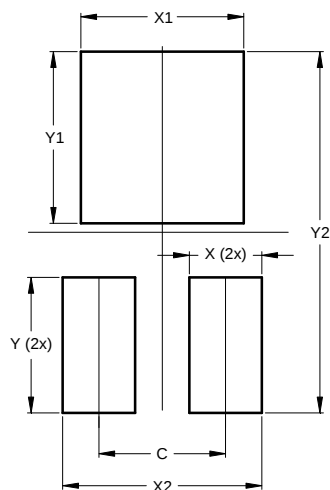
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



X2-DFN0806-3			
Dim	Min	Max	Typ
A	0.375	0.40	0.39
A1	0	0.05	0.02
A3	-	-	0.10
b	0.10	0.20	0.15
D	0.55	0.65	0.60
D1	0.35	0.45	0.40
E	0.75	0.85	0.80
E1	0.20	0.30	0.25
e	-	-	0.35
K	-	-	0.20
L	0.20	0.30	0.25
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.350
X	0.200
X1	0.450
X2	0.550
Y	0.375
Y1	0.475
Y2	1.000

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